

We claim:

Sub 1

1. In an integrated semiconductor structure having a plurality of layers, a contact structure extending through a plurality of layers and serving for electrically connecting regions of the semiconductor structure, the contact structure comprising a first contact hole filling in a first layer, a second contact hole filling in a second layer, and an intermediate structure in an intermediate layer disposed between said first layer and said second layer and connecting said first contact hole filling with said second contact hole filling, said intermediate structure forming an interconnect having a length between longitudinal ends thereof and a given width, and a contact area at each of said longitudinal ends with a contact area width greater than said given width.

2. The contact structure according to claim 1, wherein said interconnect is configured to connect two nearest points of a periodic basic grid to one another.

3. The contact structure according to claim 2, wherein said contact area of said intermediate structure is a square contact area at each end of the interconnect.

4. The contact structure according to claim 3, wherein the contact areas and the interconnect define a bone-shape form of said intermediate structure.

5. The contact structure according to claim 1, wherein said intermediate layer is a metallization plane, and said intermediate structure is formed of a conductive material of the metallization plane.

6. The contact structure according to claim 1, wherein said contact hole fillings contain tungsten.

7. The contact structure according to claim 1, wherein the first and second layers are oxide layers.

8. The contact structure according to claim 1, wherein at least one further metallization layer is formed adjacent one of the first and second layer.

9. The contact structure according to claim 1, wherein the integrated semiconductor structure is an embedded DRAM.

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